

# GSM3825EX5F

## 30V P-Channel Enhancement Mode MOSFET

### Product Description

GSM3825EX5F, P-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent  $R_{DS(ON)}$ , low gate charge.

These devices are particularly suited for low voltage power management, such as smart phone and notebook computer, and low in-line power loss are needed in commercial industrial surface mount applications.

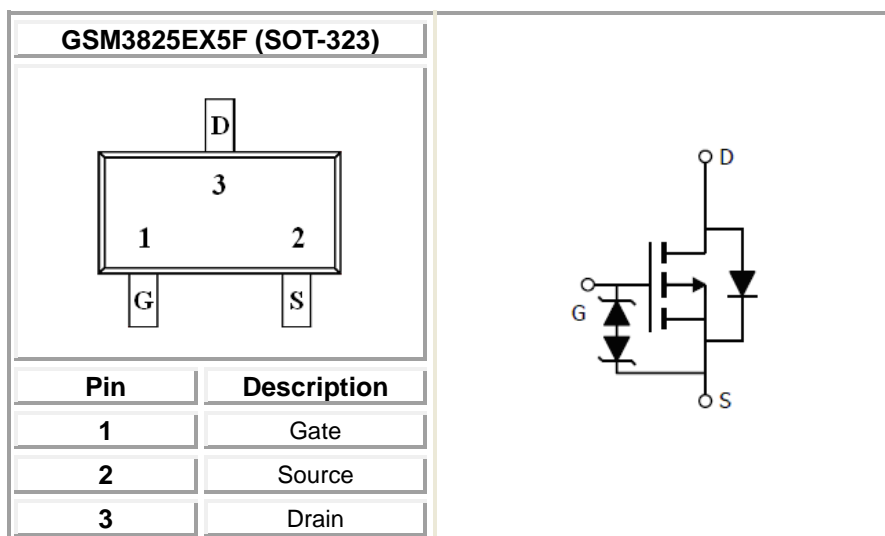
### Features

- -30V/-0.37A,  $R_{DS(ON)}=2500m\Omega@V_{GS}=-4.5V$   
 $R_{DS(ON)}=2900m\Omega@V_{GS}=-2.5V$   
 $R_{DS(ON)}=5000m\Omega@V_{GS}=-1.8V$
- Low-Voltage Operation
- High-Speed Circuits
- ESD Protection
- SOT-323 package design

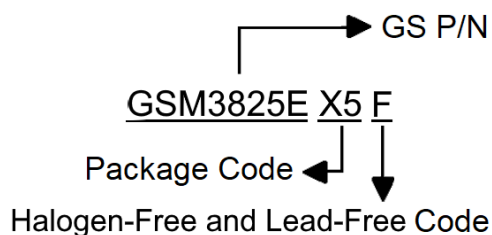
### Applications

- Drivers : Relays, Solenoids, Lamps, Hammers
- Battery Operated Systems
- Power Supply Converter Circuits
- Load/Power Switching Smart Phones, Pagers

### Packages & Pin Assignments

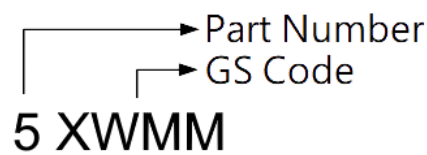


## Ordering Information



Part Number	Package	Quantity Reel
GSM3825EX5F	SOT-323	3000 PCS

## Marking Information



## Absolute Maximum Ratings

(T<sub>A</sub>=25°C unless otherwise noted)

Symbol	Parameter	Typical	Unit
V <sub>DSS</sub>	Drain-Source Voltage	-30	V
V <sub>GSS</sub>	Gate-Source Voltage	±10	V
I <sub>D</sub>	Continuous Drain Current(T <sub>J</sub> =150°C)	T <sub>A</sub> =25°C	-0.37
		T <sub>A</sub> =70°C	-0.29
I <sub>DM</sub>	Pulsed Drain Current	-1.4	A
P <sub>D</sub>	Power Dissipation	T <sub>A</sub> =25°C	0.5
		T <sub>A</sub> =70°C	0.32
R <sub>θJA</sub>	Thermal Resistance Junction to ambient	250	°C/W
T <sub>J</sub>	Operating Junction Temperature Range	-55 to +150	°C
T <sub>STG</sub>	Storage Temperature Range	-55 to +150	°C

Note1. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

## Electrical Characteristics

(T<sub>A</sub>=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static</b>						
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-30			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250uA	-0.4		-1.0	
I <sub>GSS</sub>	Gate Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±8V			±10	uA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V			-1	uA
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-0.5A		1.5	2.5	Ω
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-0.2A		1.9	2.9	
		V <sub>GS</sub> =-1.8V, I <sub>D</sub> =-0.1A		2.4	5.0	
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =-10V, I <sub>D</sub> =-0.25A		610		mS
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =-0.5A, V <sub>GS</sub> =0V			1.3	V
<b>Dynamic</b>						
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =-15V, V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-1A		1.0		nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =-15V, V <sub>GS</sub> =-8V, I <sub>D</sub> =-1A		0.2		
Q <sub>gd</sub>	Gate-Drain Charge	V <sub>DS</sub> =-15V, V <sub>GS</sub> =-8V, I <sub>D</sub> =-1A		0.1		
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V f=1MHz		54		pF
C <sub>oss</sub>	Output Capacitance			10.9		
C <sub>rss</sub>	Reverse Transfer Capacitance			5.8		
t <sub>d(on)</sub>	Turn-On Time	V <sub>DD</sub> =-10V, R <sub>L</sub> =47Ω, I <sub>D</sub> =-0.2A V <sub>GEN</sub> =-4.5V, R <sub>G</sub> =10Ω		3.8		ns
t <sub>r</sub>				11		
t <sub>d(off)</sub>	Turn-Off Time			45		
t <sub>f</sub>				20		

## Typical Performance Characteristics

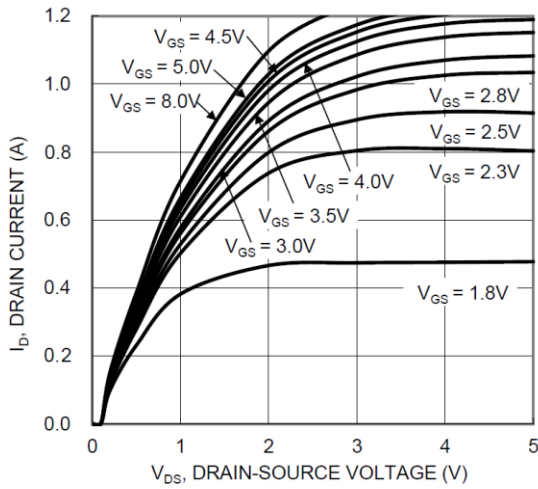


Fig. 1 Typical Output Characteristics

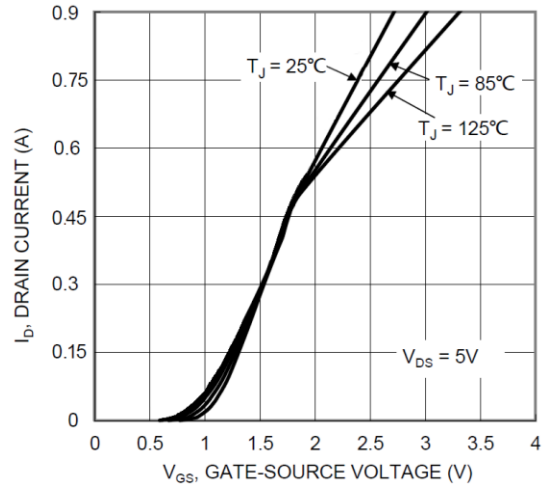


Fig. 2 Typical Transfer Characteristics

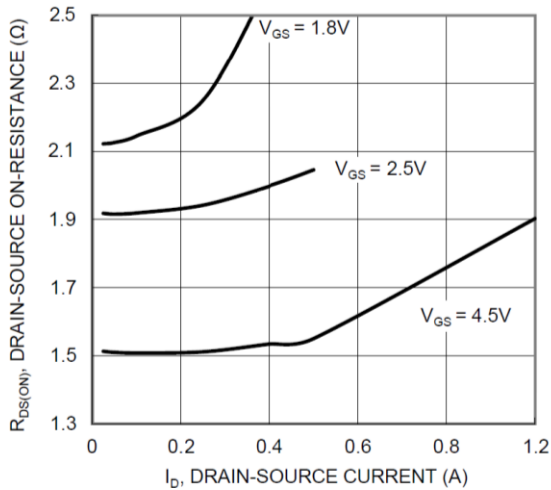


Fig. 3 Typical On-Resistance vs.  $I_D$  and  $V_{GS}$

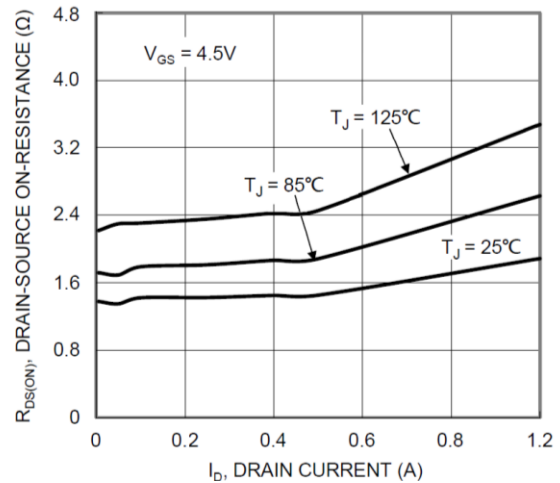


Fig. 4 Typical Drain-Source On-Resistance vs.  $I_D$  and  $T_J$

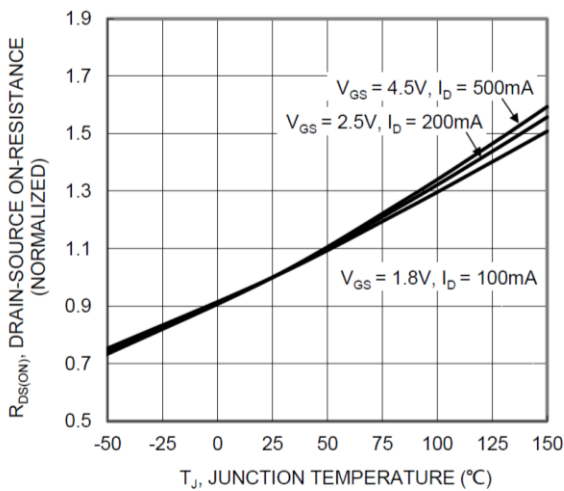


Fig. 5 On-Resistance Variation with  $T_J$

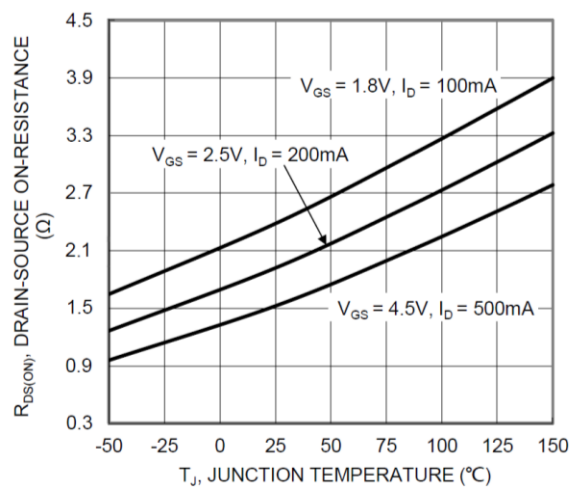


Fig. 6 On-Resistance Variation with  $T_J$

## Typical Performance Characteristics (continue)

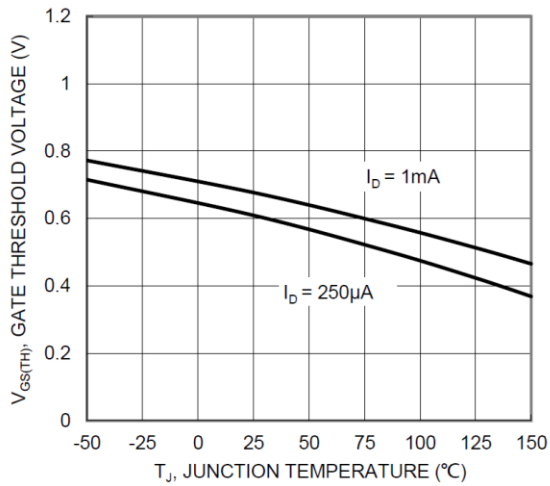


Fig. 7 Gate Threshold Variation vs.  $T_A$

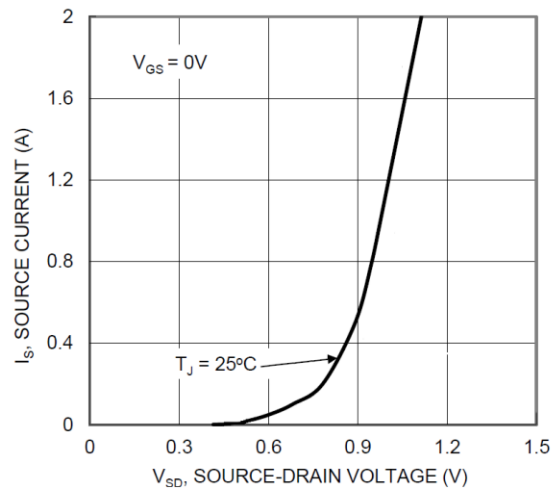


Fig. 8 Diode Forward Voltage vs. Current

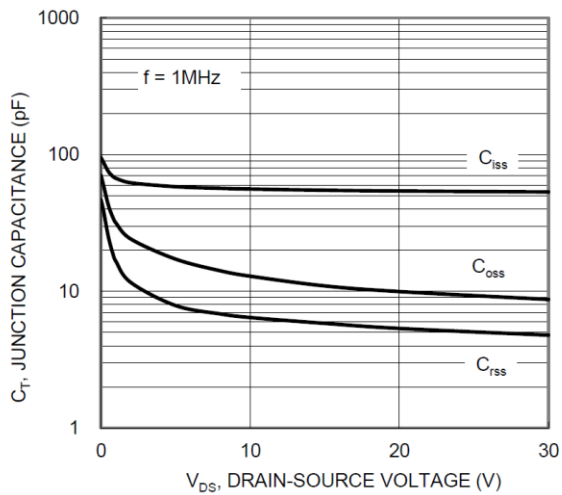


Fig. 9 Typical Capacitance

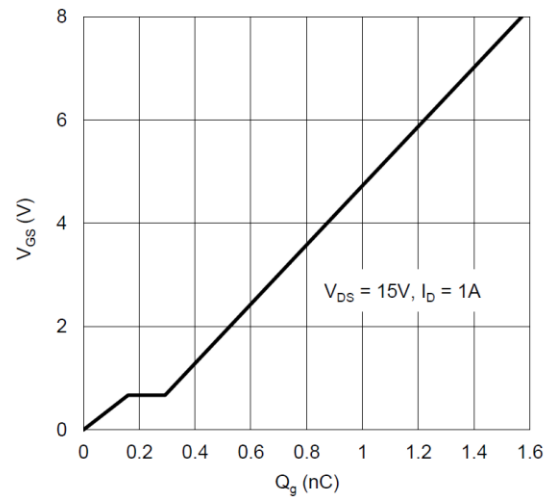


Fig. 10 Gate Charge

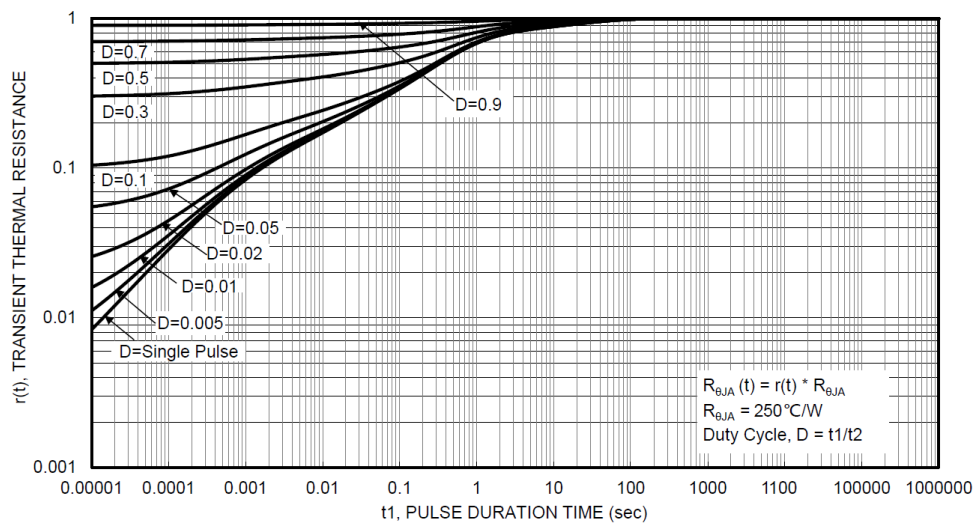
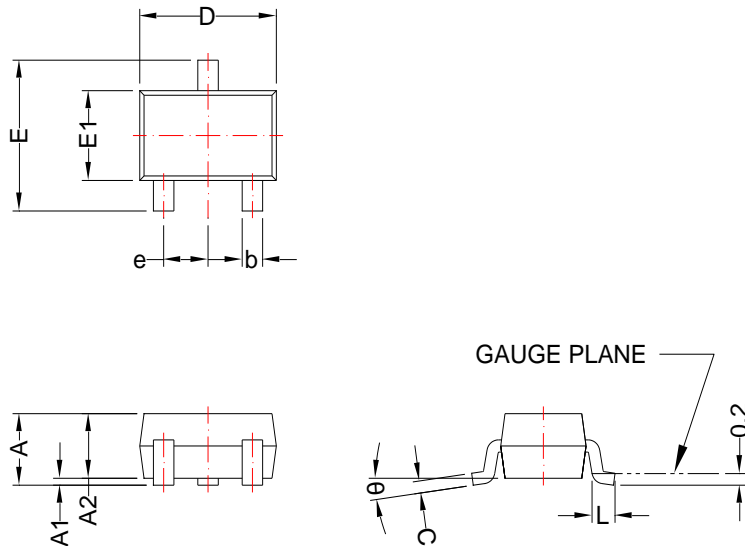


Fig. 11 Transient Thermal Response

## Package Dimension

### SOT-323



DIMENSION D DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.15 mm PER END. DIMENSION E1 DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL INTERLEAD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.25 mm PER SIDE FOR VARIATIONS WITH BODY SIZES  $\approx 3 \times 3 \text{ mm}$ . INTERLEAD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 mm FOR VARIATIONS WHERE EITHER D OR E1 IS  $< 3 \text{ mm}$ .

Dimensions				
Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	0.80	1.10	0.031	0.043
A1	0.00	0.10	0.000	0.004
A2	0.80	1.00	0.031	0.039
b	0.20	0.40	0.008	0.016
c	0.08	0.26	0.003	0.010
D	1.80	2.20	0.071	0.087
E	1.80	2.40	0.071	0.094
E1	1.15	1.35	0.045	0.053
e	0.65 BSC		0.026 BSC	
L	0.26	0.45	0.010	0.018
$\theta$	0°	8°	0°	8°





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## CONTACT US

GS Headquarter	
	4F.,No.43-1,Lane11,Sec.6,Minquan E.Rd Neihsu District Taipei City 114, Taiwan (R.O.C)
	886-2-2657-9980
	886-2-2657-3630
	sales_twn@gs-power.com

RD Division	
	824 Bolton Drive Milpitas. CA. 95035
	1-408-457-0587